Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC converter
- Portable Equipment
- Power management

General Description:

The XRS75N10F uses super trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is PDFN5060-8L, which accords with the ROHS standard and Halogen Free standard.

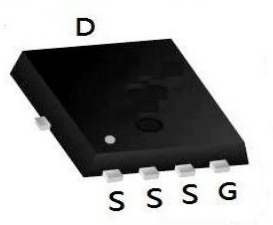
100% DVDS Tested
100% Avalanche Tested

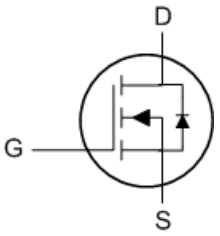
Product Summary

Green

BVDSS	RDSON	ID
100V	6.2mΩ	75A

PDFN5060-8L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1,6]	75	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1,6]	51	A
I_{DM}	Pulsed Drain Current[2]	320	A
EAS	Single Pulse Avalanche Energy[3]	150	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25°C	Total Power Dissipation[4]	108	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	1.15	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	60	°C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10 V, I_D=20A	---	6.2	7.75	mΩ
		V_{GS}=4.5V , I_D=10A	---	7.6	8.36	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.3	1.8	2.3	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=100V, V_{GS}=0V , T_J=100℃	---	---	---	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=15A	---	---	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.65	---	Ω
Q_g	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_D=20A	---	32.1	---	nC
Q_{gs}	Gate-Source Charge		---	9.7	---	
Q_{gd}	Gate-Drain Charge		---	8.6	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V,ID=20A, R_G = 4Ω, V_{GS}=10V	---	15	---	ns
T_r	Rise Time		---	23	---	
$T_{d(off)}$	Turn-Off Delay Time		---	45	---	
T_f	Fall Time		---	35	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	1916	---	pF
C_{oss}	Output Capacitance		---	602	---	
C_{rss}	Reverse Transfer Capacitance		---	17	---	

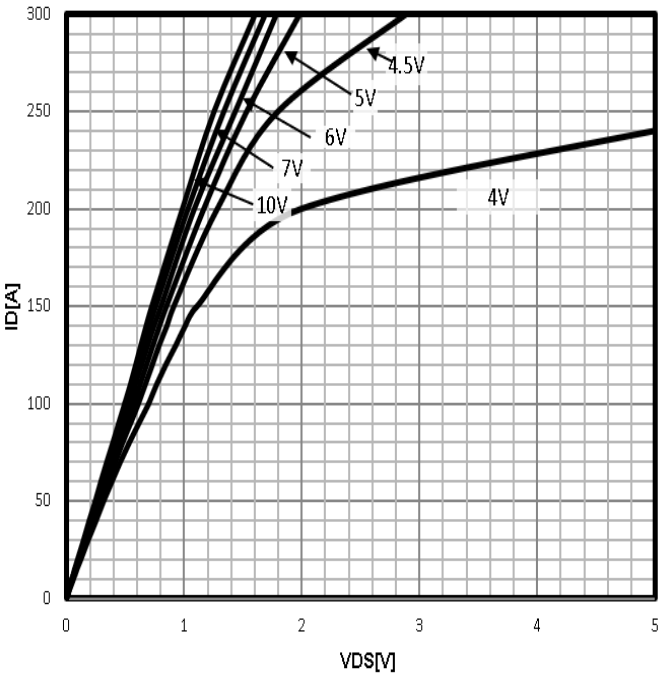
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	75	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=20A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=20A ,di/dt=100A / μs , T_J= 25 ℃	---	60	---	nS
Q_{rr}	Reverse Recovery Charge		---	110	---	nC

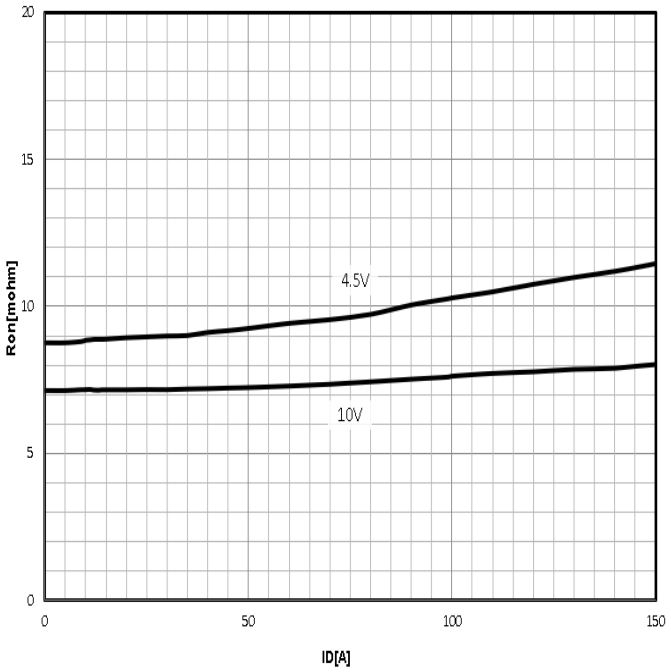
a1: Repetitive rating; pulse width limited by maximum junction temperature
a2: VDD=50V, L=0.3mH, Rg=25Ω, Starting TJ=25 ℃

Characteristics Curve:

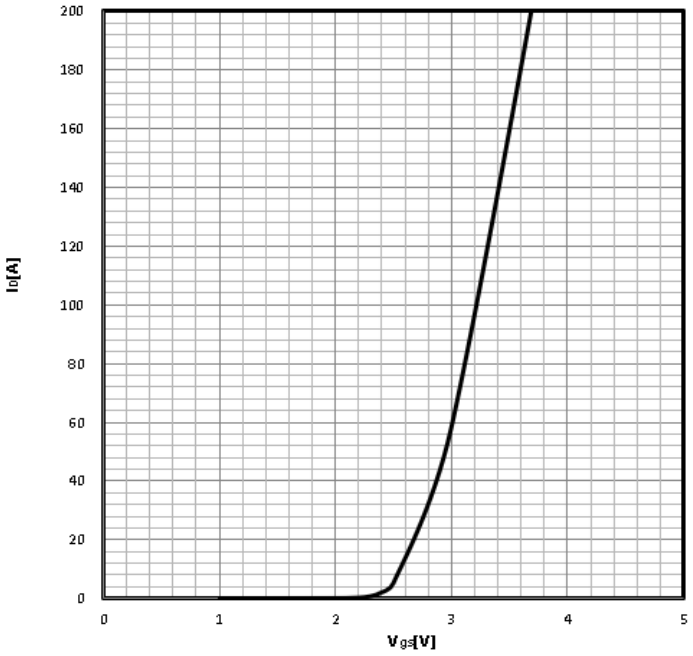
Typ. output characteristics
$I_D=f(V_{DS})$



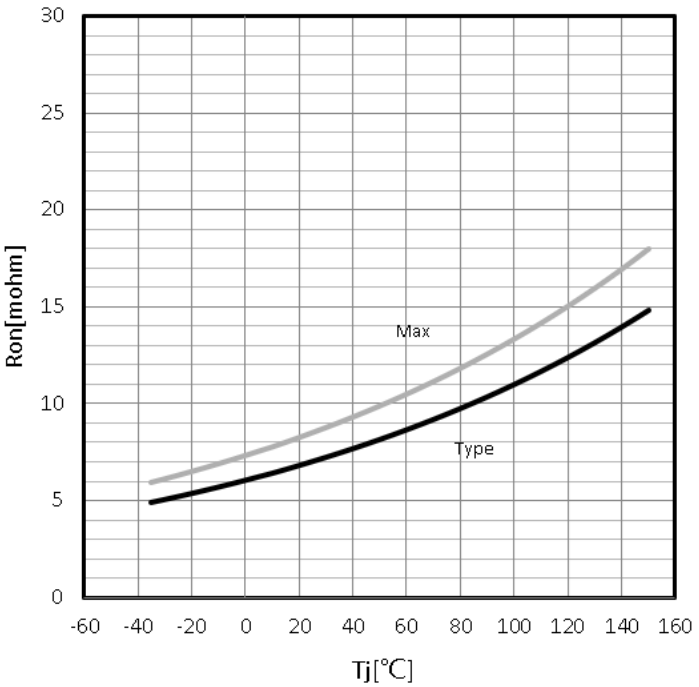
Typ. drain-source on resistance
$R_{DS(on)}=f(I_D)$



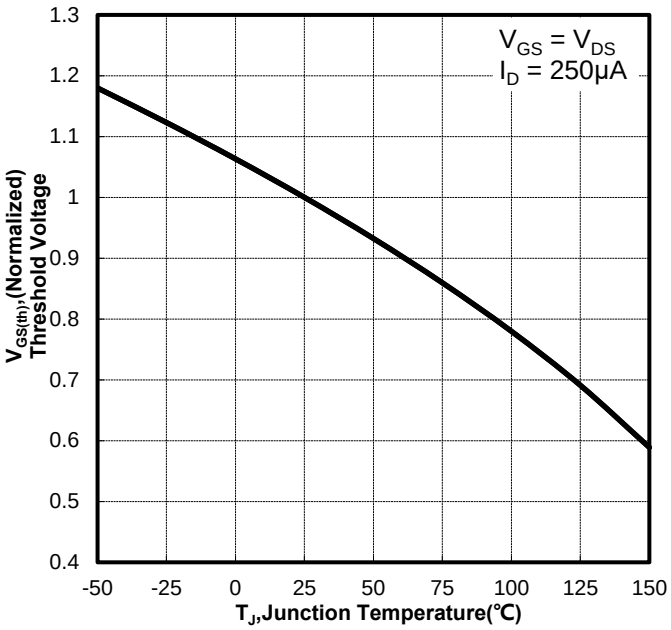
Typ. transfer characteristics
$I_D=f(V_{GS})$



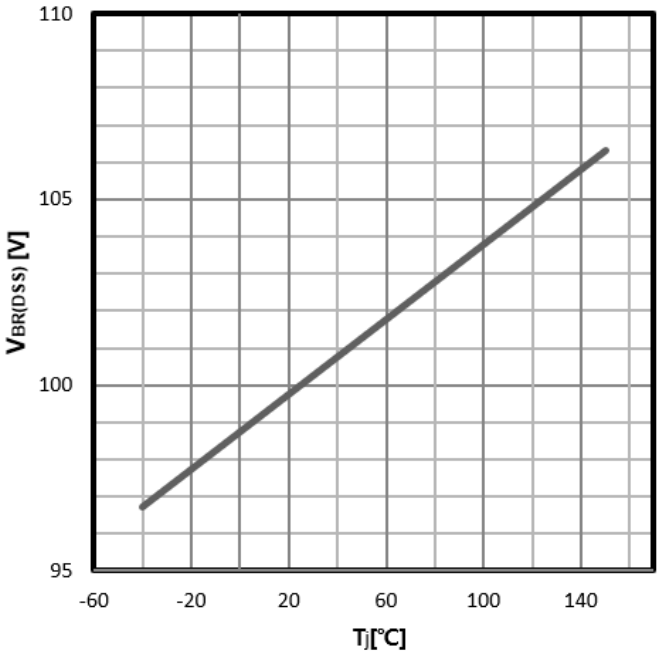
Drain-source on-state resistance
$R_{DS(on)}=f(T_j);I_D=20A;\ V_{GS}=10V$



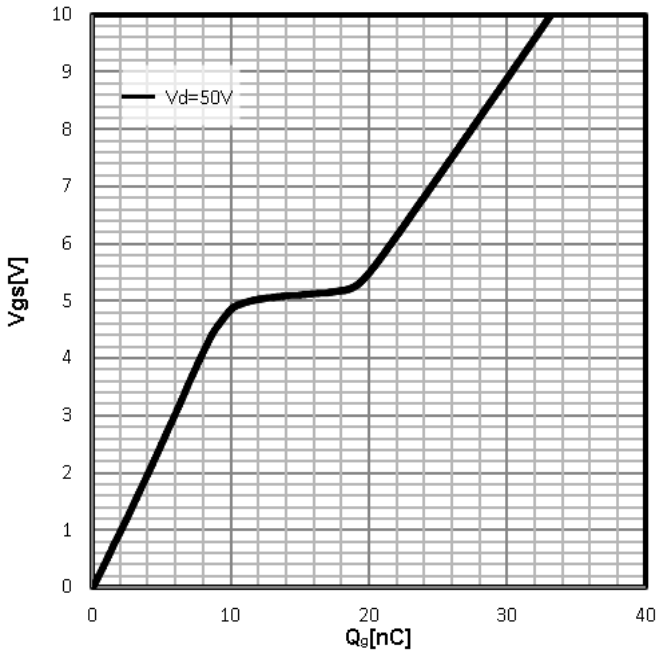
Gate Threshold Voltage
$V_{TH}=f(T_j)$; I_D=250uA



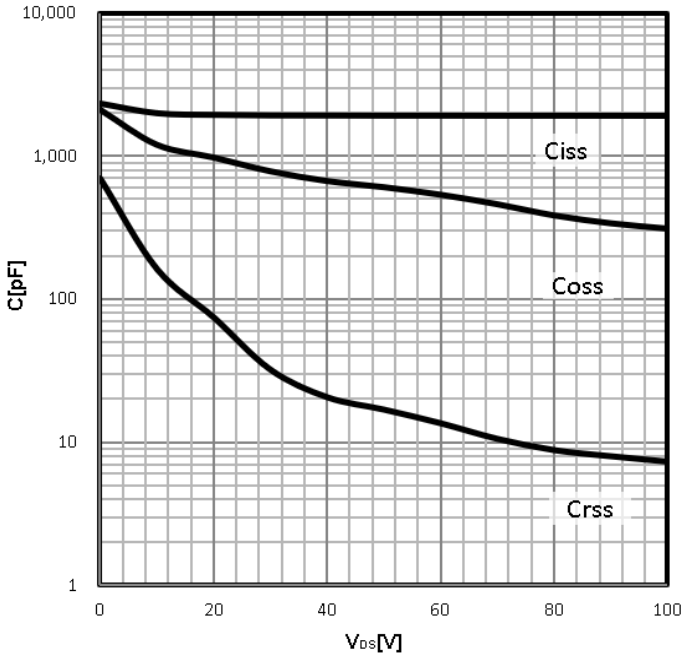
Drain-source breakdown voltage
$V_{BR(DSS)}=f(T_j)$; I_D=250uA



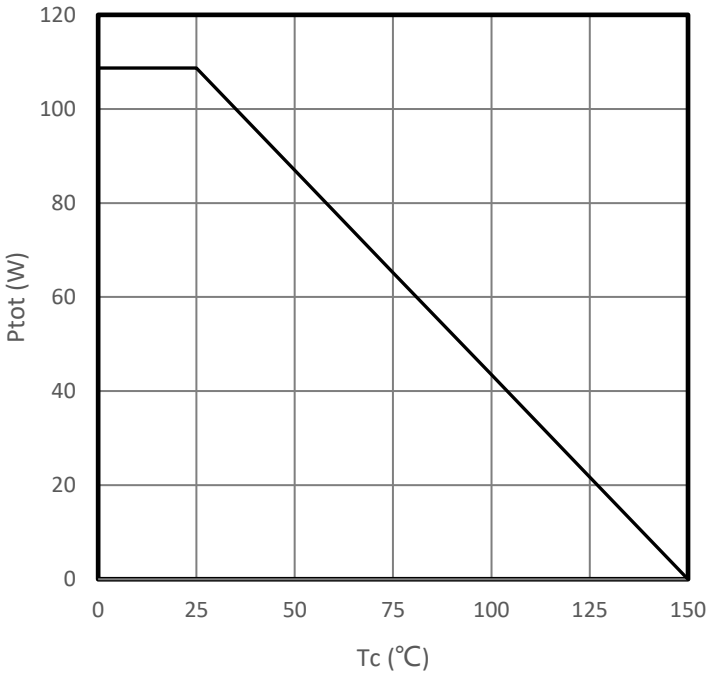
Typ. gate charge
$V_{GS}=f(Q_g)$; I_D=20A



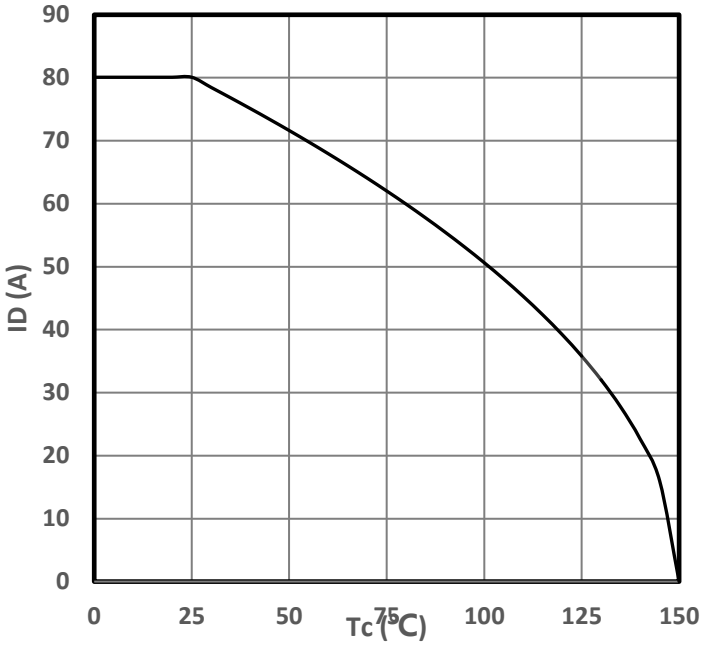
Typ. capacitances
C =f(V_{DS}); V_{GS}=0V; f =1MHz



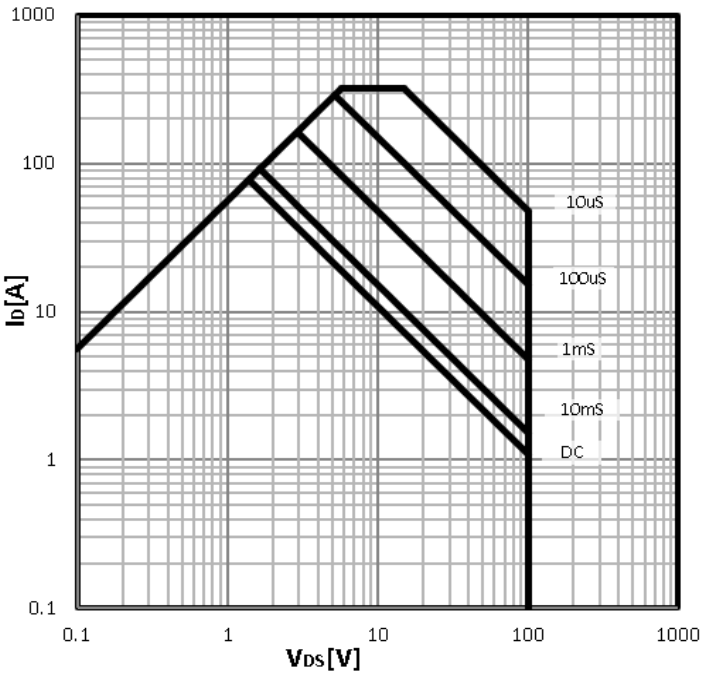
Power Dissipation
$P_{tot}=f(T_C)$



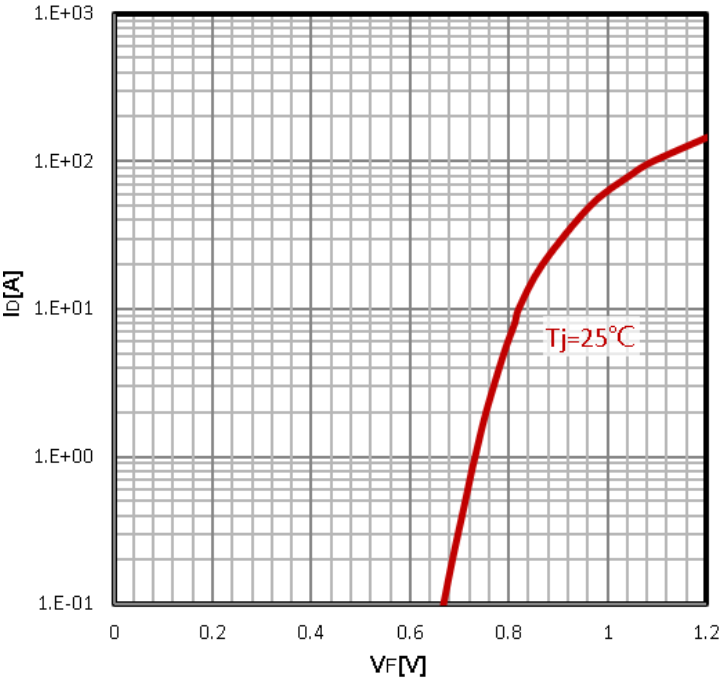
Maximum Drain Current
$I_D=f(T_C)$



Safe operating area
$I_D=f(V_{DS})$

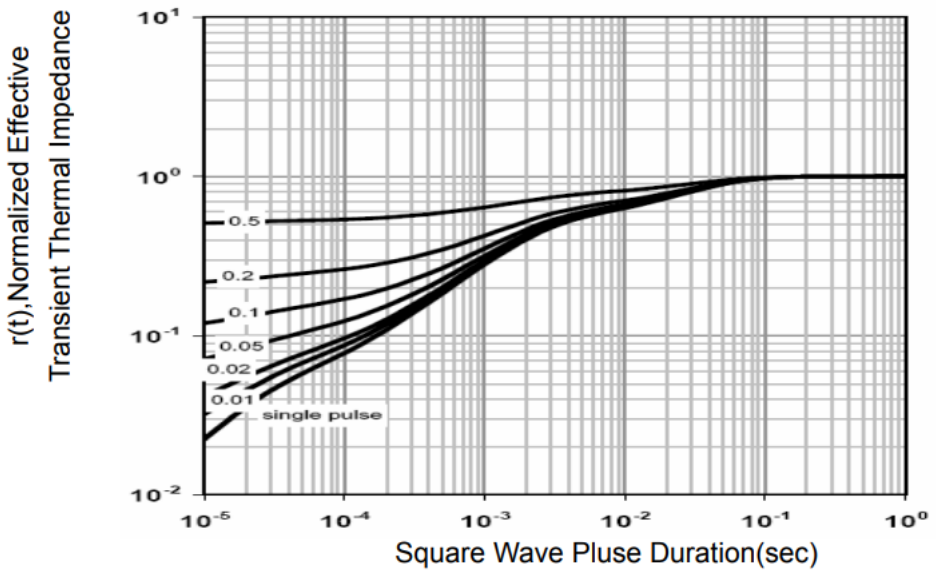


Body Diode Forward Voltage Variation
$I_F=f(V_{GS})$

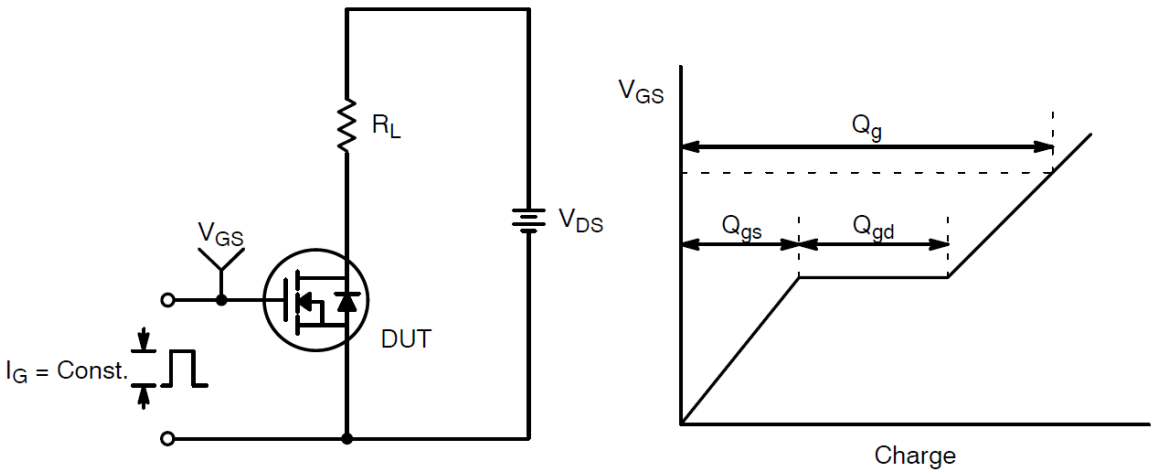


Max. transient thermal impedance

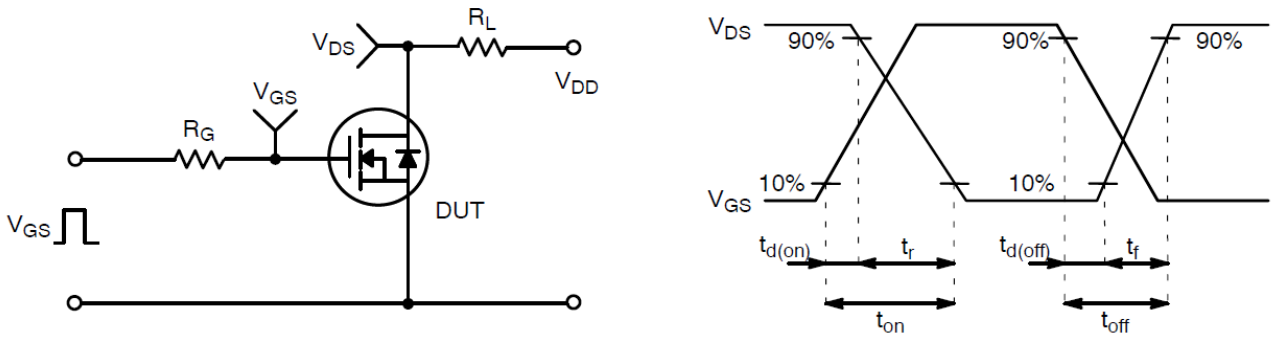
$Z_{thJC}=f(t_p)$



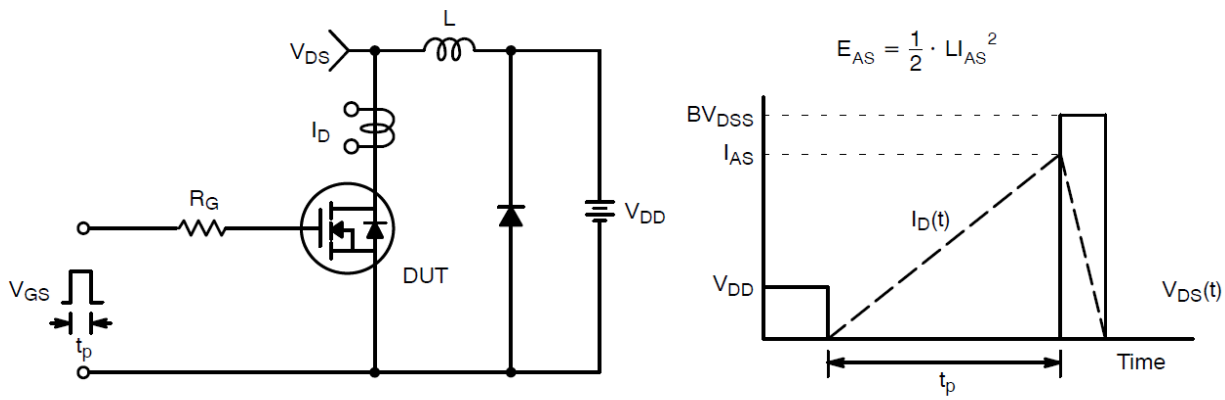
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform

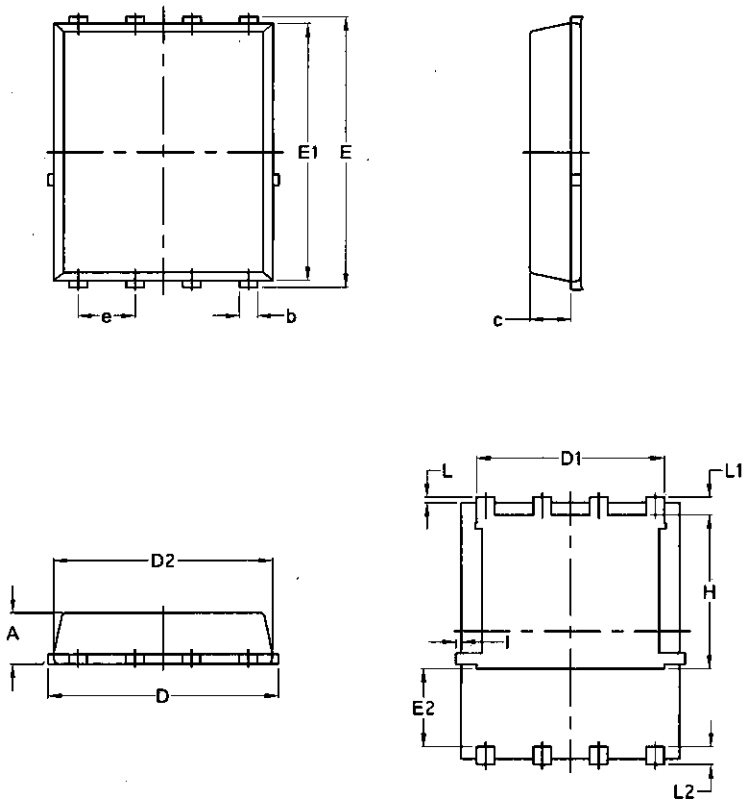


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-PDFN5060-8L-Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070